PHIL_BJT $r_o = 10,91814\text{k}\Omega$ $V_A = 51,82703\text{V}$ $I_{C_{sat}} = 4,746873\text{mA}$
SIEMENS $r_o = 18,26616\text{k}\Omega$ $V_A = 88,60728\text{V}$ $I_{C_{sat}} = 4,850897\text{mA}$
modelo modificado $r_o = 17,34281\text{k}\Omega$ $V_A = 90,66048\text{V}$ $I_{C_{sat}} = 4,963302\text{mA}$
transistor 1 $r_o = 19,97264\text{k}\Omega$ $V_A = 86,67009\text{V}$ $I_{C_{sat}} = 4,339440\text{mA}$
transistor 2 $r_o = 22,66700\text{k}\Omega$ $V_A = 107,6684\text{V}$ $I_{C_{sat}} = 4,615188\text{mA}$
transistor 3 $r_o = 23,13776\text{k}\Omega$ $V_A = 104,6125\text{V}$ $I_{C_{sat}} = 4,653361\text{mA}$